

Part 2: Next-generation server power designs with integrated GaN technology

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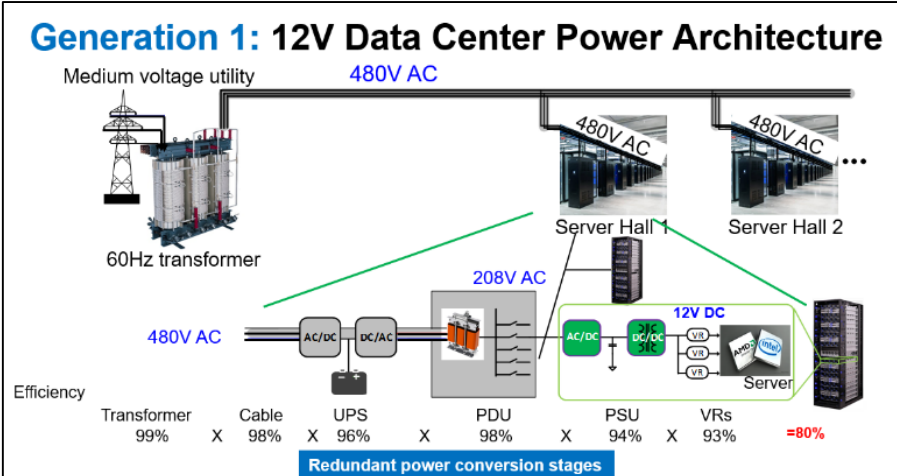
Agenda

- Server power system evolution
- TI presence in server power
- Server power supply unit deep dive
 - PFC stage
 - ISO DC/DC stage
- Server power controllers
 - Server main power stage controller
 - Server aux supply controller
- Q&A

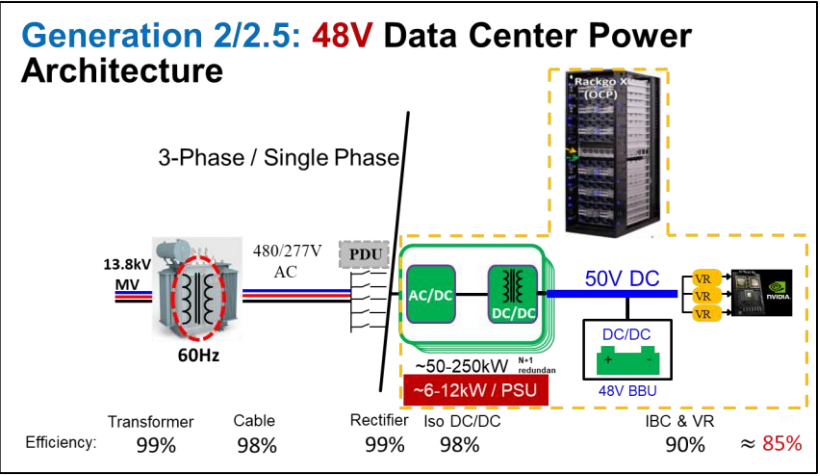


Please feel free to share your questions on “chat.” We will also have 10 minutes of live Q&A towards the end of the presentation

Server PSU market trends and challenges

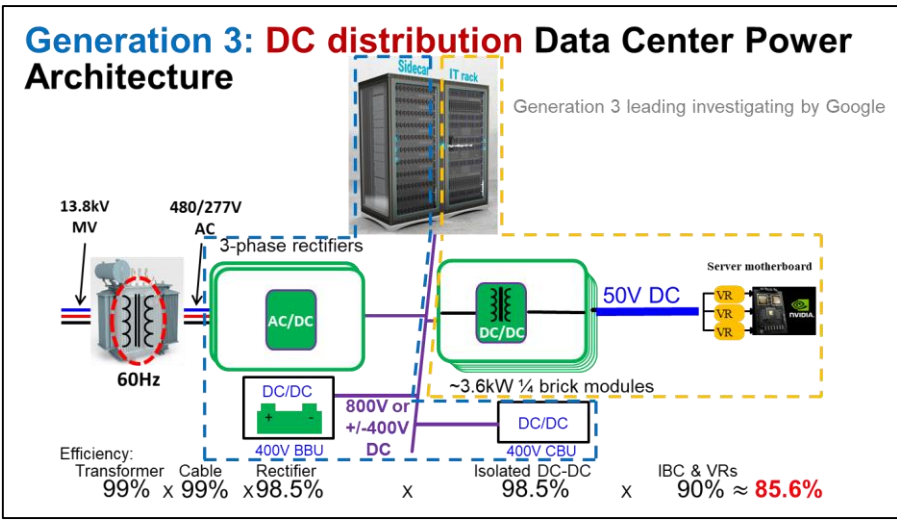


1990s – Now: Traditional rack servers (CRPS)

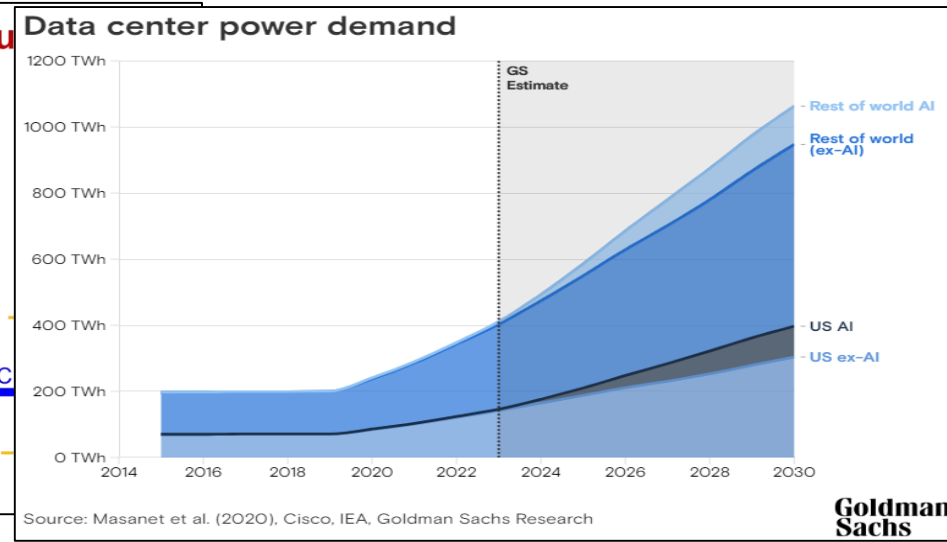
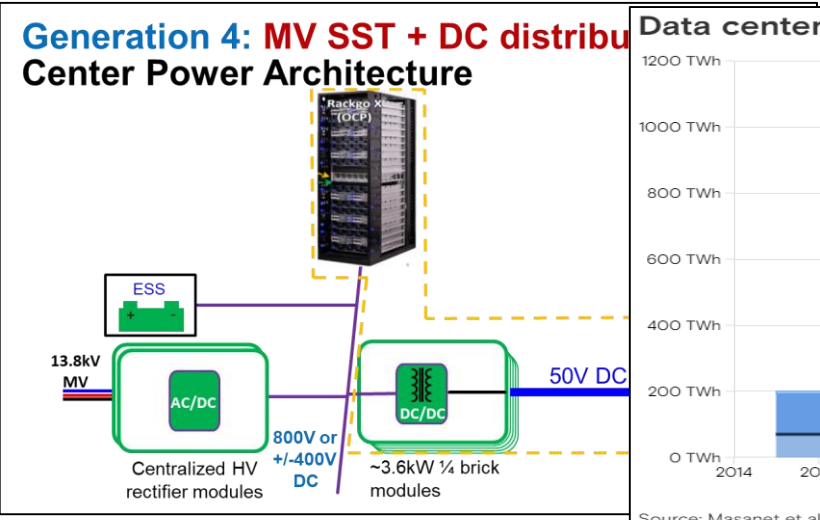


2016 – 2027: Cloud/AI computing (Open rack)

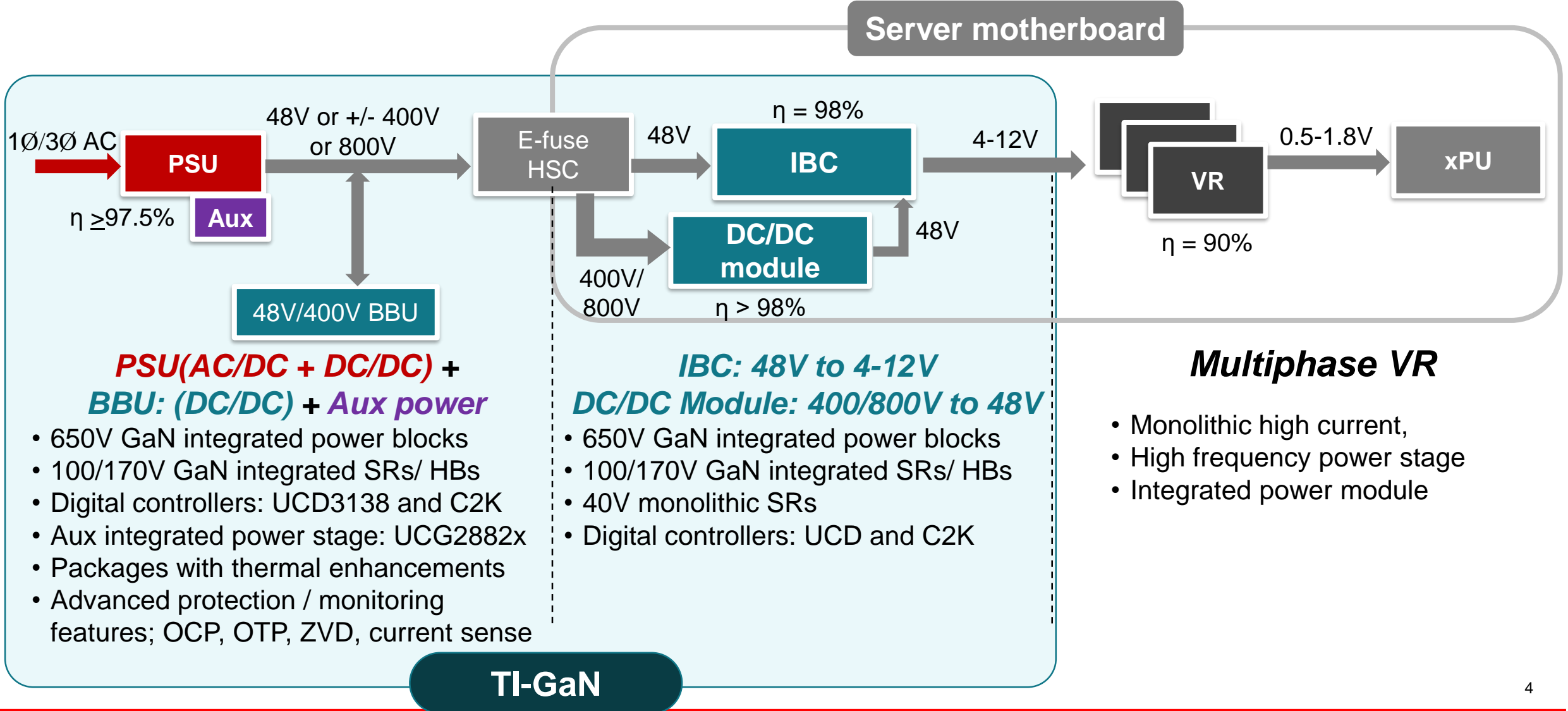
- ➔ Efficiency
- ➔ Power consumption
- ➔ Size
- ➔ Power density



2027 onwards

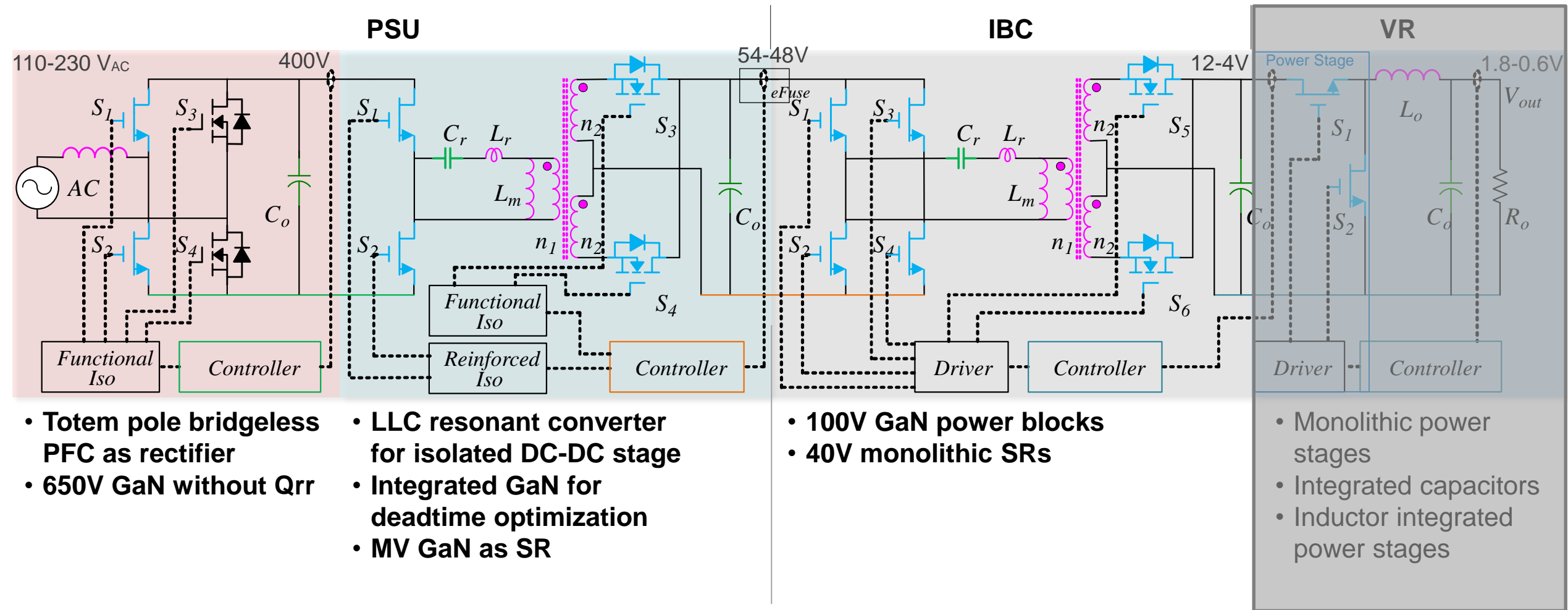


TI solutions from grid to gate – Gen 2 & 3 architectures



Server power delivery

GaN in server power (Gen 2 architecture)



- Totem pole bridgeless PFC as rectifier
- 650V GaN without Qrr

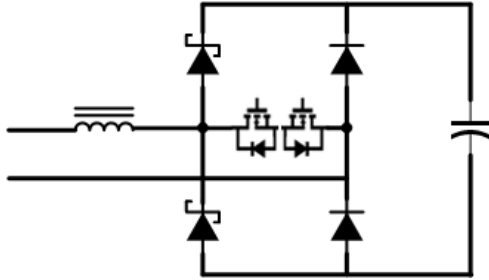
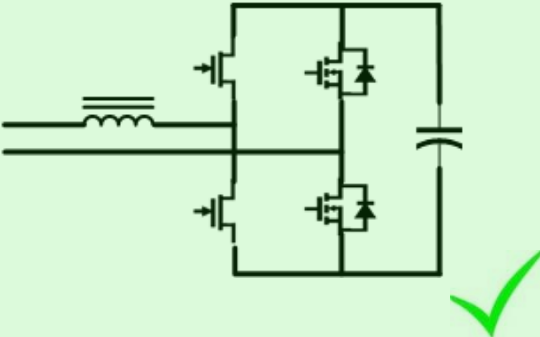
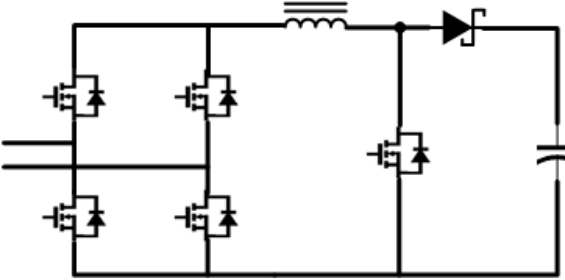
- LLC resonant converter for isolated DC-DC stage
- Integrated GaN for deadtime optimization
- MV GaN as SR

- 100V GaN power blocks
- 40V monolithic SRs

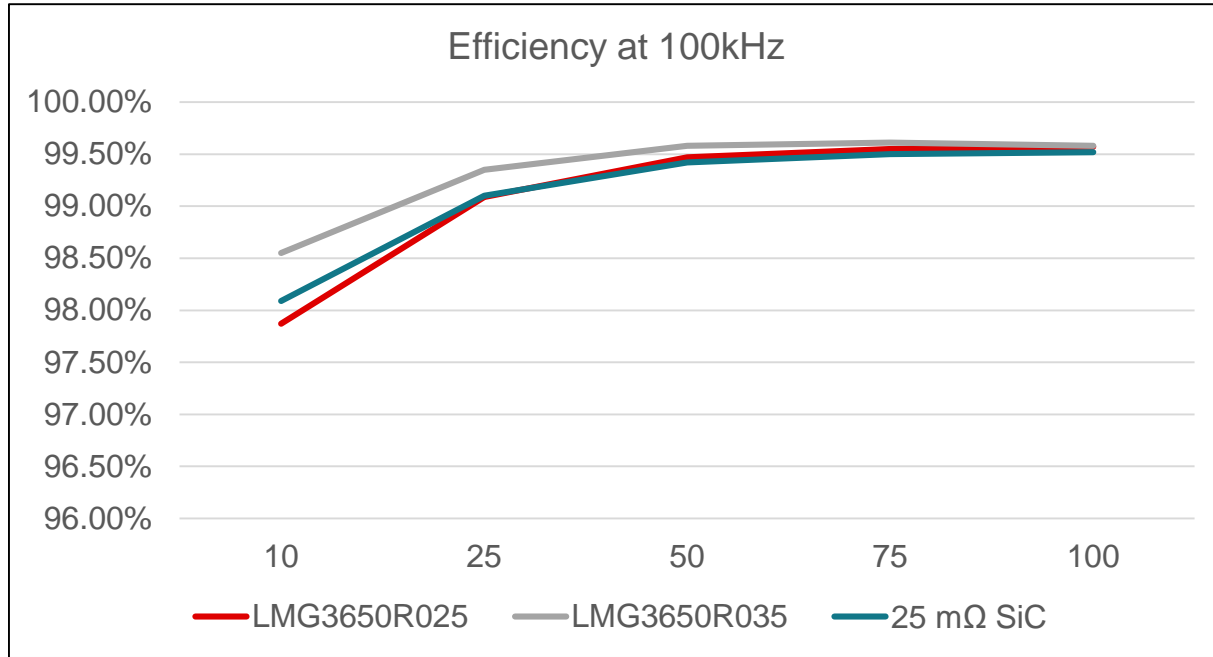
- Monolithic power stages
- Integrated capacitors
- Inductor integrated power stages

PFC

Which is the most efficient PFC architecture?

	AC switch PFC	Totem-pole PFC	Active bridge PFC
Block diagram			
Details	2 silicon diodes 2 MOSFETs 2 silicon diodes or SiC diodes 1 choke coil	2 GaN FETs or SiC MOSFETs 2 MOSFETs 1 choke coil	5 MOSFETs 1 SiC diode 1 choke coil
Cost	Medium	Low	High
Efficiency	On-time: 2 MOSFETs Off-time: 1 SiC diode + 1 silicon diode	On-time: 1 MOSFET + 1 FET Off-time: 1 MOSFET + 1 FET	On-time: 3 MOSFETs Off-time: 2 MOSFETs + 1 diode
	~98.7%	~99.0%	~98.5%

LMG3650R0XX vs 25mΩ SiC (100kHz)



Conclusion: LMG3650R035 has a better loss performance at mid load and full load due to lower switching loss combined with better performance on Qrr loss.

Test conditions:

- 2ph Totempole CCM PFC
- 4.5kW, 240Vac, 400Vdc
- 100kHz, 2ph. design
- Tamb = 55degC

	LMG3650R025	LMG3650R035	25mΩ SiC
Rdson, typ at 25C [mohm]	24	35	25
Coss(tr) [pF]	458	299	322

LMG3650R025

Load (%)	Device Conduction Power Loss (W)	Device Coss Power Loss (W)	Overlap Power Loss (W)	Deadtime Loss (W)	Switching Loss (W)	Driver Loss (W)	Total Loss per Device (W)	Efficiency (%)
10	0.016	2.300	0.029	0.013	2.329	0.086	2.443	97.87%
25	0.103	2.300	0.072	0.032	2.372	0.086	2.592	99.09%
50	0.422	2.300	0.143	0.065	2.443	0.086	3.016	99.47%
75	1.092	2.300	0.215	0.100	2.515	0.086	3.793	99.55%
100	2.072	2.300	0.286	0.136	2.586	0.086	4.880	99.57%

LMG3650R035

Load (%)	Device Conduction Power Loss (W)	Device Coss Power Loss (W)	Overlap Power Loss (W)	Deadtime Loss (W)	Switching Loss (W)	Driver Loss (W)	Total Loss per Device (W)	Efficiency (%)
10	0.022	1.500	0.029	0.013	1.529	0.086	1.650	98.55%
25	0.142	1.500	0.072	0.032	1.572	0.086	1.832	99.35%
50	0.591	1.500	0.143	0.066	1.643	0.086	2.386	99.58%
75	1.412	1.500	0.215	0.103	1.715	0.086	3.315	99.61%
100	2.736	1.500	0.286	0.141	1.786	0.086	4.749	99.58%

25mΩ SiC

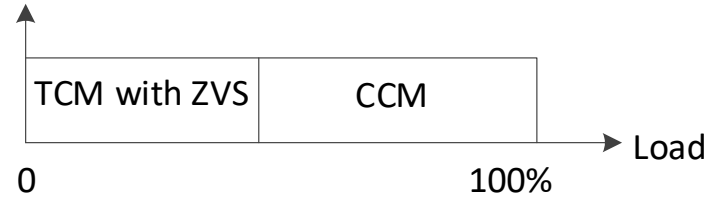
Load (%)	Device Conduction Power Loss (W)	Device Coss Power Loss (W)	Overlap Power Loss (W)	Deadtime Loss (W)	Switching Loss (W)	Driver Loss (W)	Qrr Loss (W)	Total Loss per Device (W)	Efficiency (%)
10	0.013	1.800	0.057	0.022	1.857	0.172	0.121	2.185	98.09%
25	0.082	1.800	0.143	0.055	1.943	0.172	0.302	2.554	99.10%
50	0.335	1.800	0.286	0.111	2.086	0.172	0.605	3.308	99.42%
75	0.771	1.800	0.430	0.168	2.230	0.172	0.907	4.247	99.50%
100	1.409	1.800	0.573	0.227	2.373	0.172	1.210	5.390	99.52%

*Due to slow switching compared to GaN, SiC overlap loss is 2x GaN loss
 ** Due to higher driving strength for SiC FET, SiC driver loss is 2x GaN loss

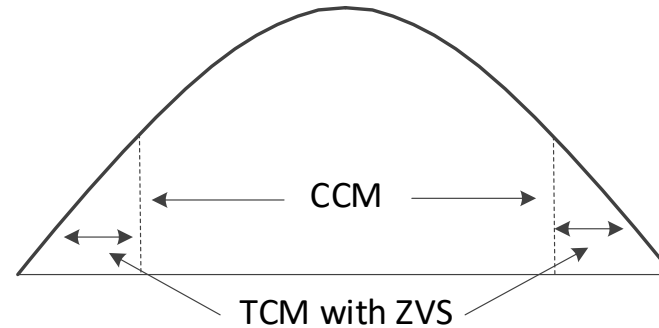
PFC mode of operation: CCM vs. TCM

	CCM operation	TCM operation
Pros	<ul style="list-style-type: none">• Low inductor current ripple• Simple control	<ul style="list-style-type: none">• Zero voltage switching (ZVS)
Cons	<ul style="list-style-type: none">• Hard switching – high switching loss	<ul style="list-style-type: none">• High inductor current ripple• Require multi-phase interleaved to reduce current ripple for high power applications:<ul style="list-style-type: none">❖ low power density❖ high cost• Complex control

Why multi-mode PFC: CCM/TCM multi-mode operation



Multi-mode at different load



Multi-mode in AC half cycle

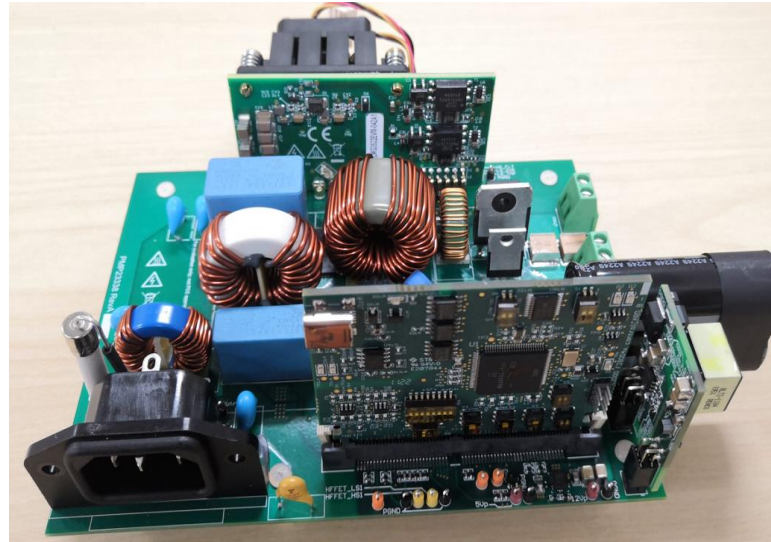
Combine the advantages of CCM and TCM:

- Higher efficiency than CCM
 - ZVS when in TCM
- Higher power density and lower cost than interleaved TCM
 - Single phase
- Easier control than TCM
 - Same controller works for both CCM and TCM

PMP23537 CCM/TCM multi-mode controlled TTPL bridgeless PFC design

Features

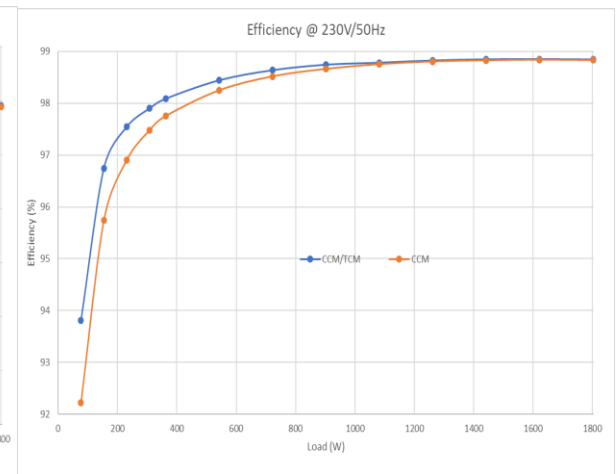
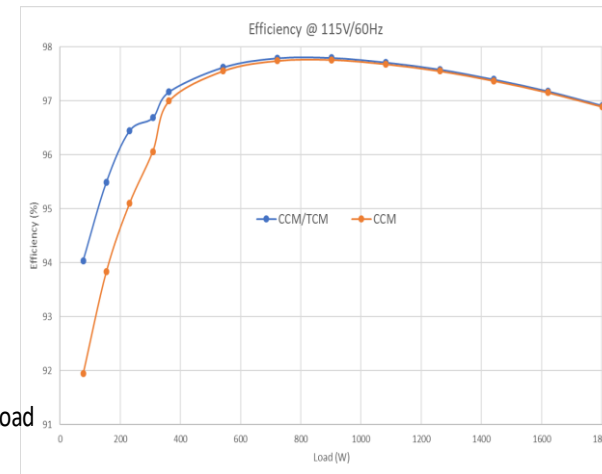
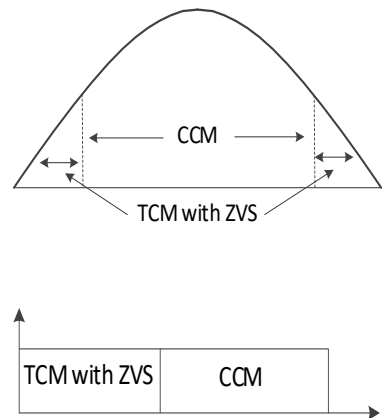
- CCM/TCM-ZVS multi-mode control in each AC half cycle. Light load efficiency is improved up to 2%
- TI GaN with integrated zero current sensing
- Single current sensor for both PFC control and e-metering with >99.5% accuracy
- Includes baby boost to extend holdup time and reduce bulk cap
- Re-rush current control when AC comes back from dropout



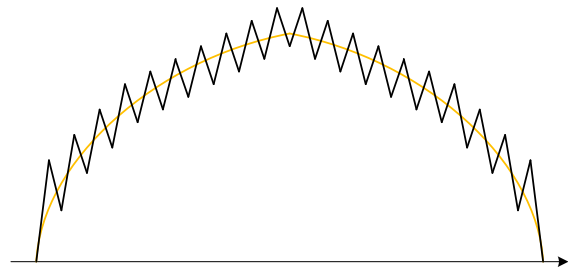
Parameter

Specification

Input voltage	85-265VAC
Output voltage	385VDC
Output power	3.6KW
Topology	Totem-pole PFC
IC	LMG3427R30, AMC1306, TMS320F28003x, TMCS1133, UCC27712, TPSM863252, UCC21220

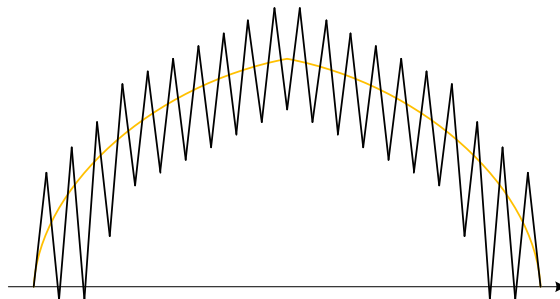


Efficiency comparison summary



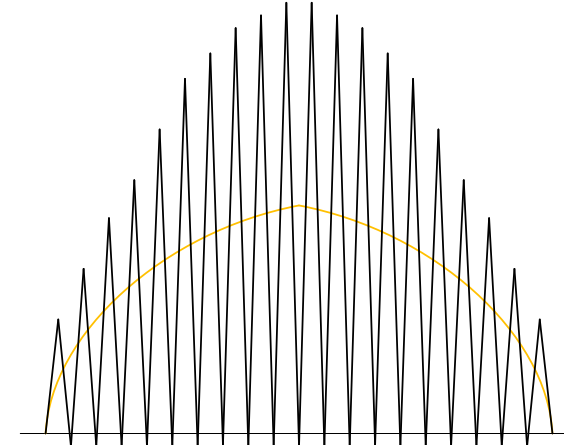
CCM: Continuous conduction mode

1-phase



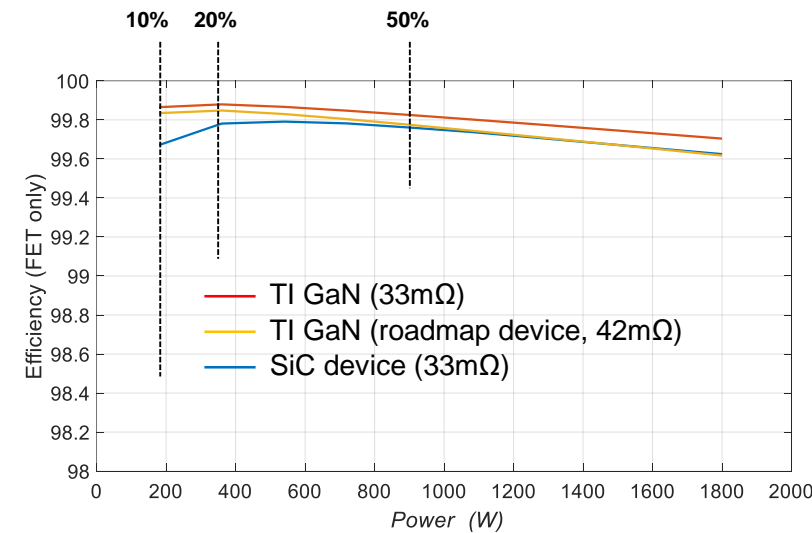
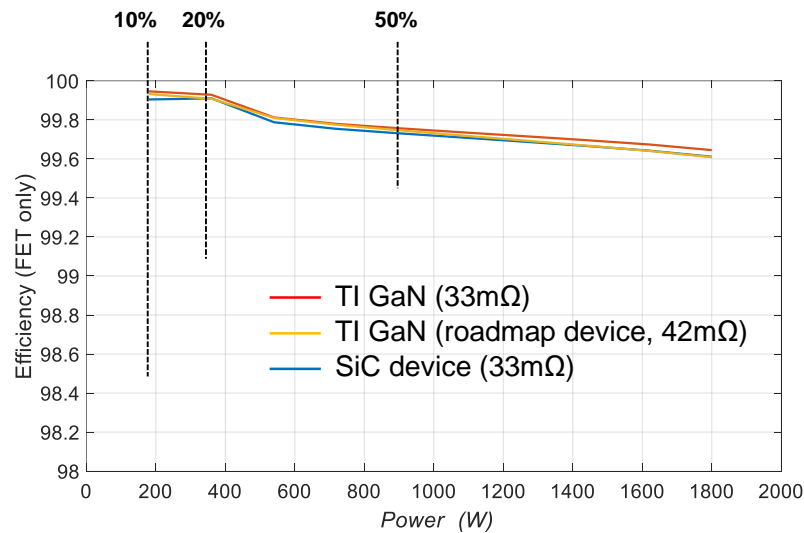
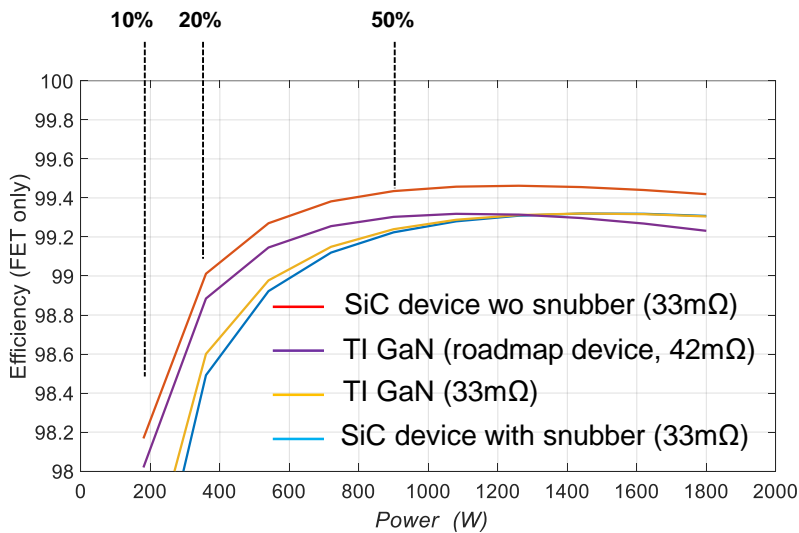
Multi-mode: CCM + TcM

$L = 150\mu\text{H}$, 1-phase



TcM: Triangular current mode

$L = 25\mu\text{H}$, 1-phase



Parameter	Comp. SiC	TI GaN	TI GaN
Ron at 25C	33mΩ	33mΩ	42mΩ
Half-load η	99.2% - 99.4%	99.2%	99.3%

Parameter	Comp. SiC	TI GaN	TI GaN
Ron at 25C	33mΩ	33mΩ	42mΩ
Half-load η	99.73%	99.76%	99.75%

Parameter	Comp. SiC	TI GaN	TI GaN
Ron at 25C	33mΩ	33mΩ	42mΩ
Half-load η	99.76%	99.82%	99.78%

ISO DC/DC

Which is the most efficient ISO DC/DC architecture?

	PSFB	FB-LLC with FB-secondary
Block diagram		
Cost	Medium	Low
Efficiency	up to 98%	~98.5%
High frequency operation	Not suited beyond 200Khz	Can go 500Khz+
Control & sync.	Simpler	Slightly complicated as it works in a tight load and frequency range
EMI	Slightly complicated EMI management	Better performance

LLC stage 2.3KW(FB- primary, FB- secondary) – Design & device parameters

Inputs:

Primary Topology: Full-Bridge

Secondary Topology: Full-Bridge

Number of output Rectifiers: 2

Number of Parallel SRs / Rectifier: 2

Input Voltage, V_{in} : 400 V

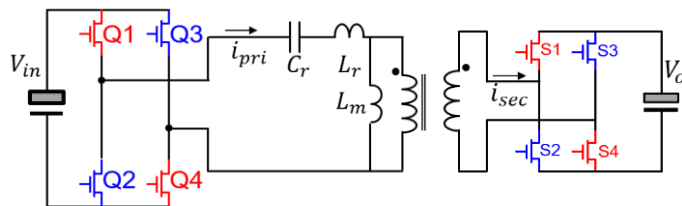
Output Voltage, V_o : 48 V

Output Power, P_o : 2300 W → 1ph.

Switching Frequency, f_s : 100 kHz

Magnetizing Inductance, L_m : 500 uH

Deadtime, t_d : 100 ns



Primary side device: HV Si-MOSFET

V_{ds} (V) = 650

R_{dson} (mOhm) = 27 @ 25 oC

R_{dson} (mOhm) = 52.6 @ 125 oC

Q_g (nC) = 108

V_{gs} (V) = 10

E_{off}^* (uJ) = 1.8 *Turn-off Energy - Eoss @10A turn-off

C_{oss} (pF) = 1604 @ V_{in}

Secondary side device: MV Si-MOSFET

V_{ds} (V) = 80

R_{dson} (mOhm) = 1.9 @ 25 oC

R_{dson} (mOhm) = 3.04 @ 125 oC

Q_g (nC) = 31

V_{gs} (V) = 10

C_{oss} (pF) = 1200 @ V_{in}

Body Diode Forward Voltage (V) = 0.82

Primary side device: LMG3650R025

V_{ds} (V) = 650

R_{dson} (mOhm) = 24 @ 25 oC

R_{dson} (mOhm) = 43.2 @ 125 oC

Q_g (nC) = 119

V_{gs} (V) = 12

E_{off}^* (uJ) = 0.3 *Turn-off Energy - Eoss @10A turn-off

C_{oss} (pF) = 458 @ V_{in}

Secondary side device: LMG3100R017

V_{ds} (V) = 100

R_{dson} (mOhm) = 1.7 @ 25 oC

R_{dson} (mOhm) = 2.41 @ 125 oC

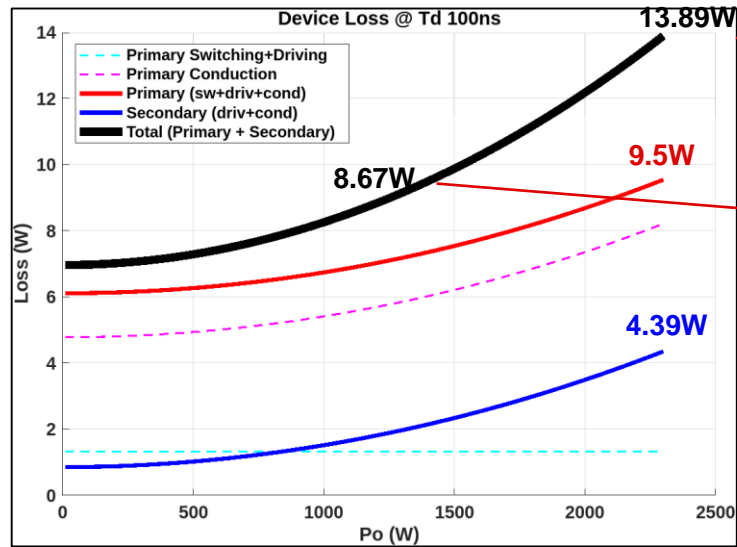
Q_g (nC) = 20

V_{gs} (V) = 5

C_{oss} (pF) = 1547 @ V_{in}

Body Diode Forward Voltage (V) = 1.5

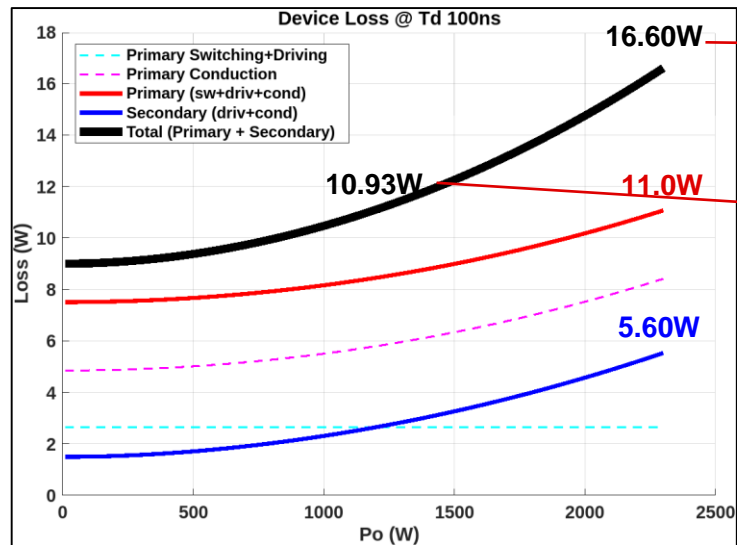
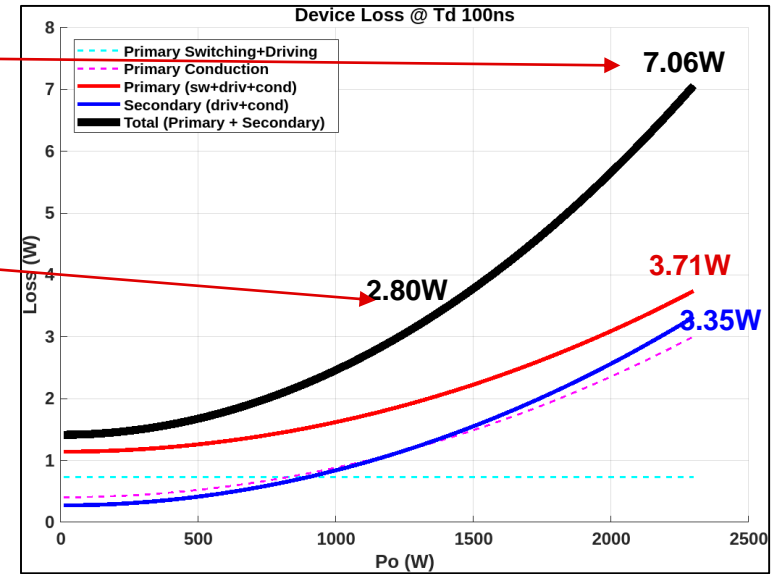
650V Si-MOSFET + 80V Si-MOSFET vs. LMG3650R025 + LMG3100R017



49.2% lower

67.7% lower

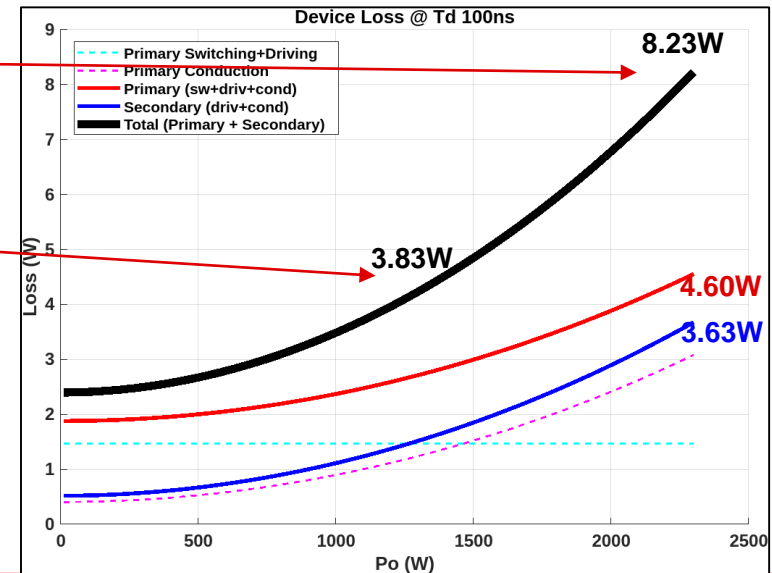
100KHz



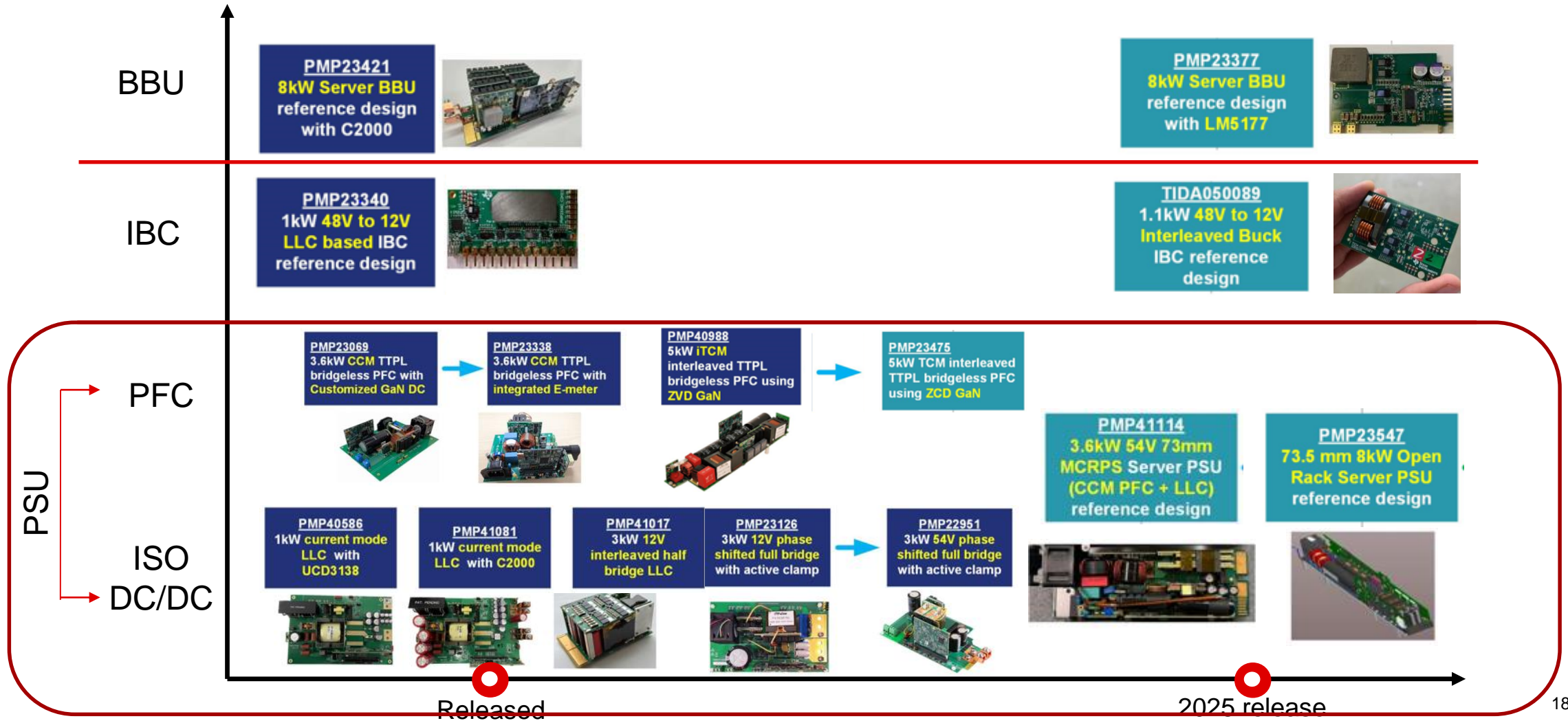
50.4% lower

64.95% lower

200KHz

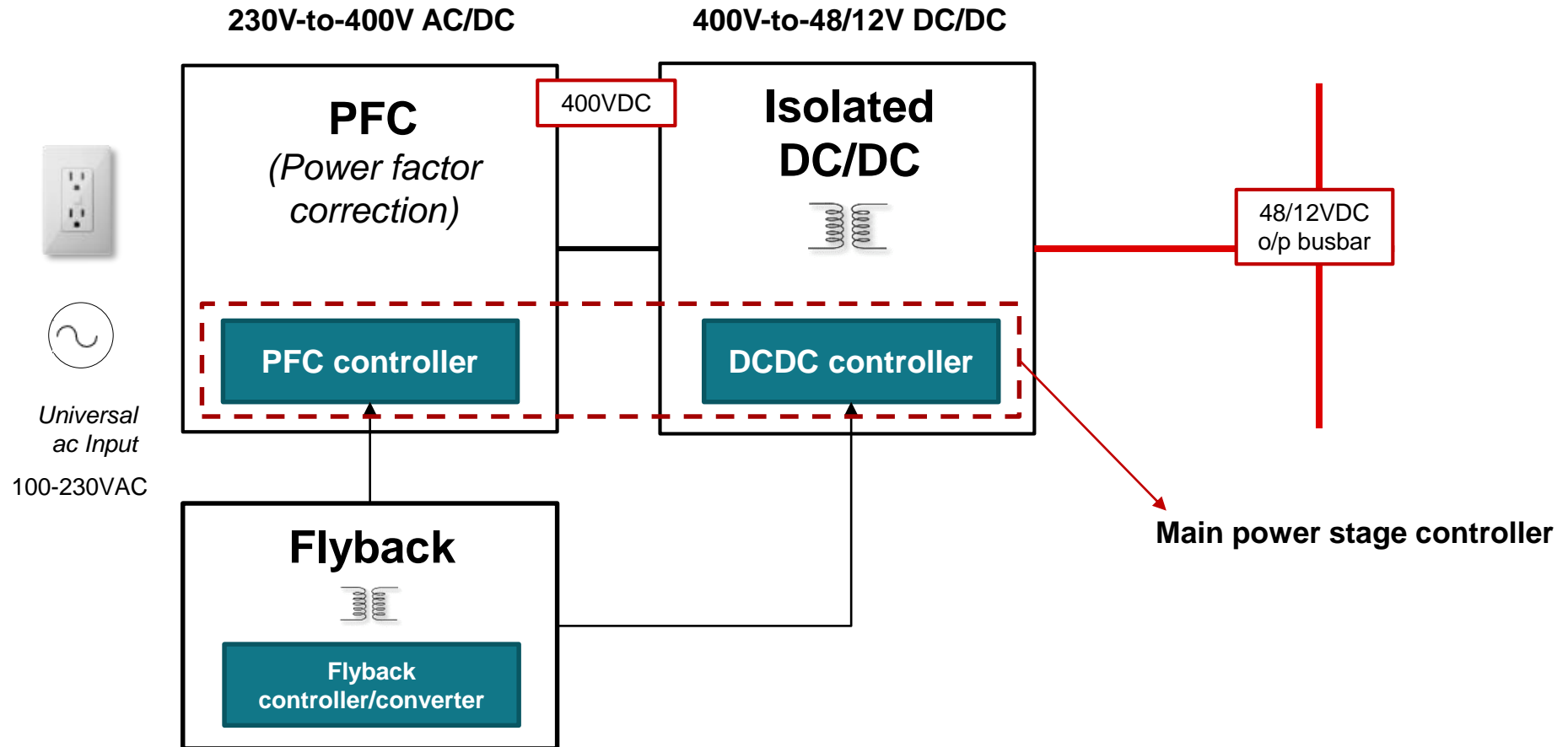


Server PSU, BBU and IBC reference designs



Controllers in the server PSU

Typical server power supply control uses individual controllers at each stage



Increasing power density driving digital control in main power stage

Power supply

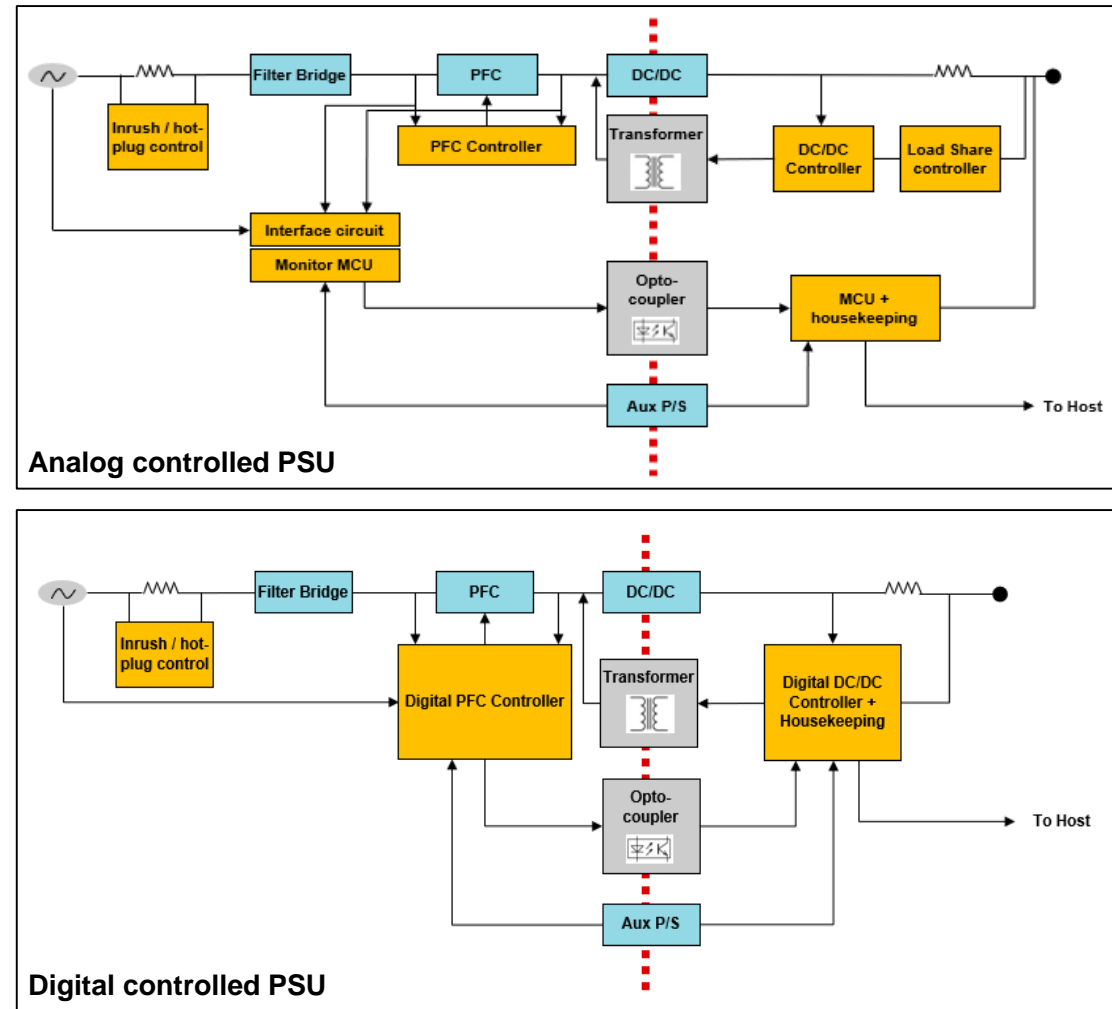
Basic power supply control

- Output regulation vs. line/load variations
- Fault protection

Housekeeping and system communication

- Thermal management
- Fan speed control
- Comms. With host MCU
- Enabling special operating modes (ex: light load, stand-by)
- Telemetry (P_{in} , V_{in} , I_{in} , temp)

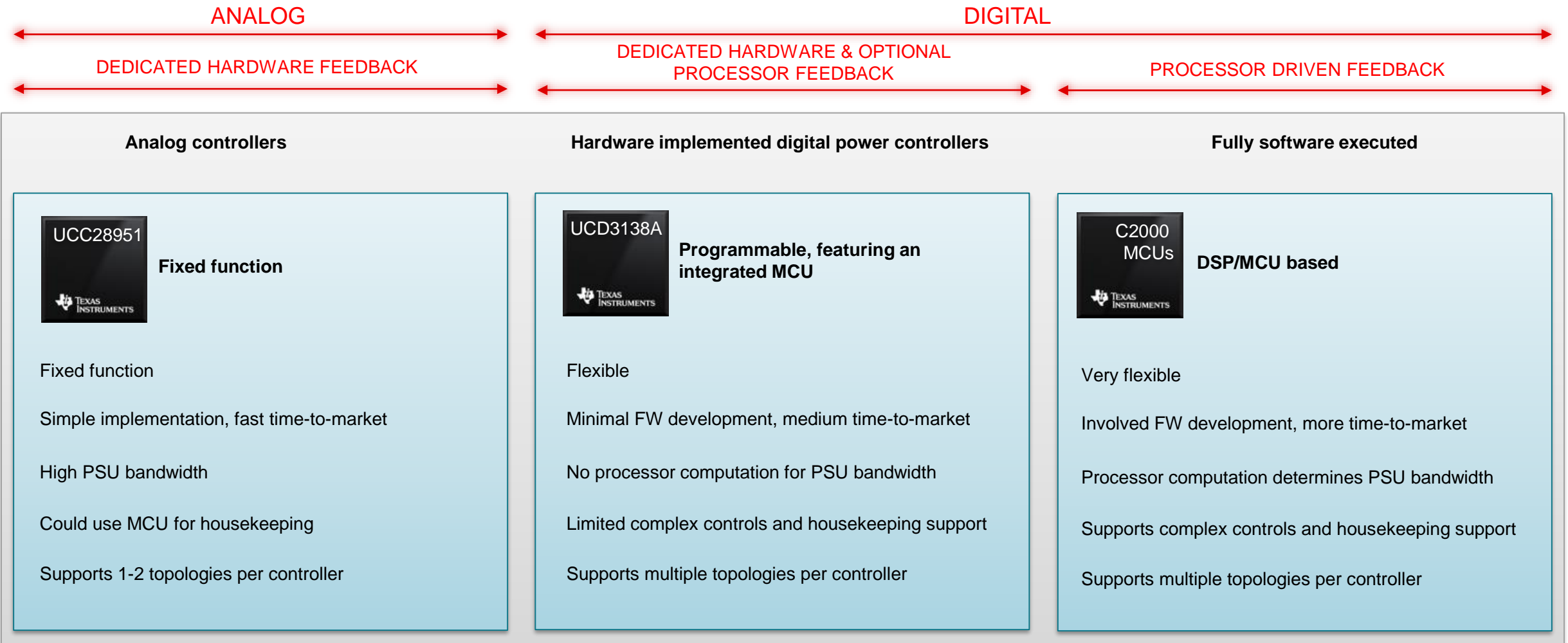
A typical power supply includes basic power control and system housekeeping



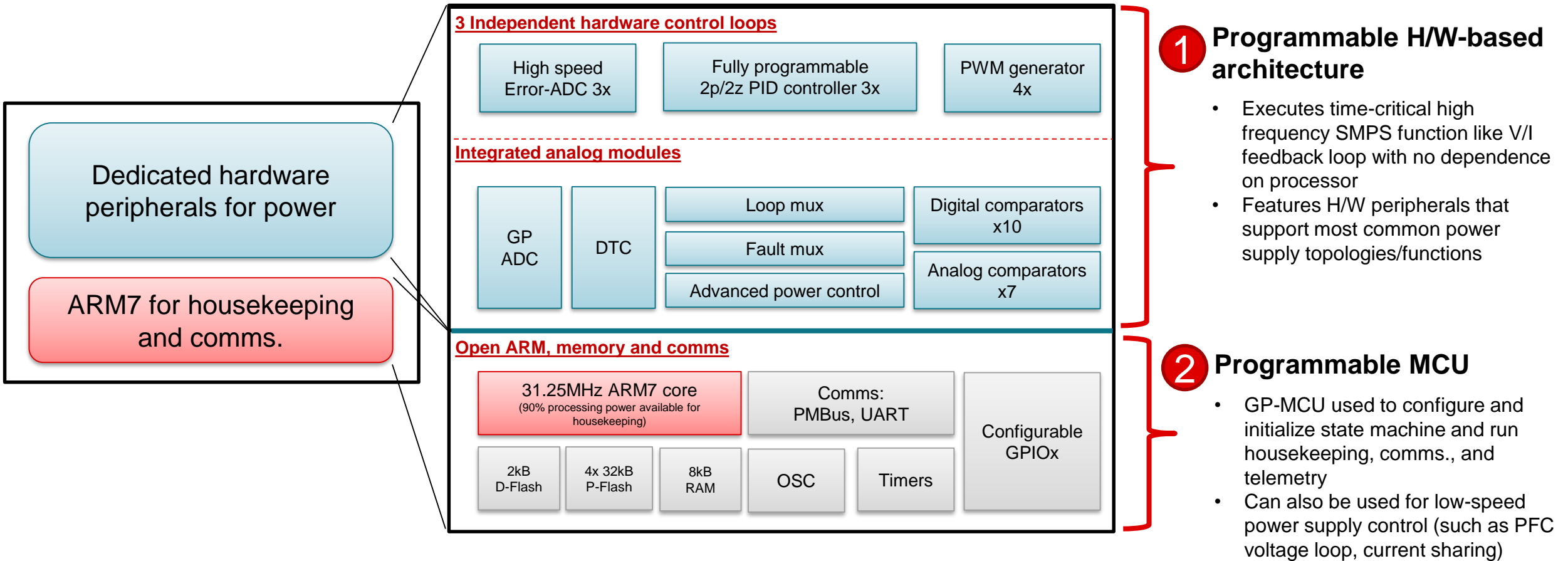
Traditionally, analog controllers took care of the **basic power supply control** and another **MCU** would take care of the **housekeeping**: More components and manufacturing cost

Power supplies with digital controllers house **both functions into the same IC** and enables multi-threaded applications: One design/device, multiple PSUs

Key controller architectures in server main power stage



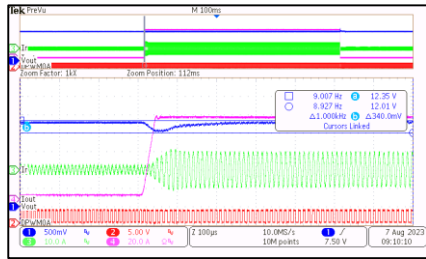
UCD3138A – Digital controller for server power



*Example block diagram shows UCD3138128A

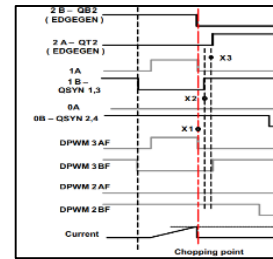
UCD3138A features specific to server power

Ultra-fast transient response



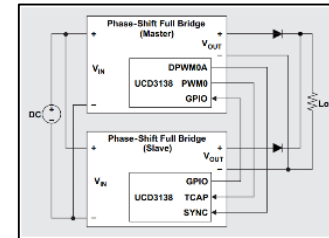
Hardware-etched peripherals → low output capacitance, smaller magnetics

Power converter fault handling



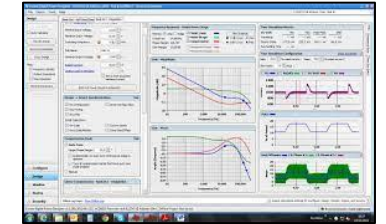
Analog/digital faults → flexibility to handle CBC or latched faults

Current sharing and synchronization



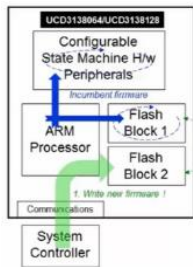
Synchronization & load sharing → modularity & superior EMI perf.

Fusion GUI for easy development



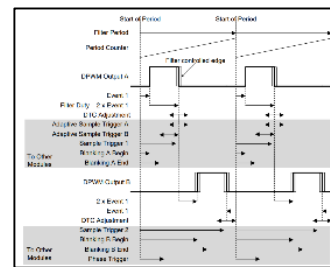
Blackbox development with GUI → faster time-to-market and superior debug capability

On-the-fly firmware upgrade



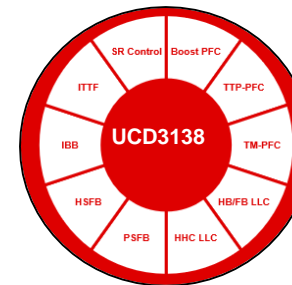
Dual memory bank architecture → zero downtime firmware update

Advanced high Res. PWMs



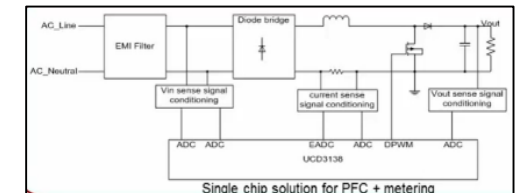
250ps resolution PWM outputs → lower output ripple

Multi-topology support



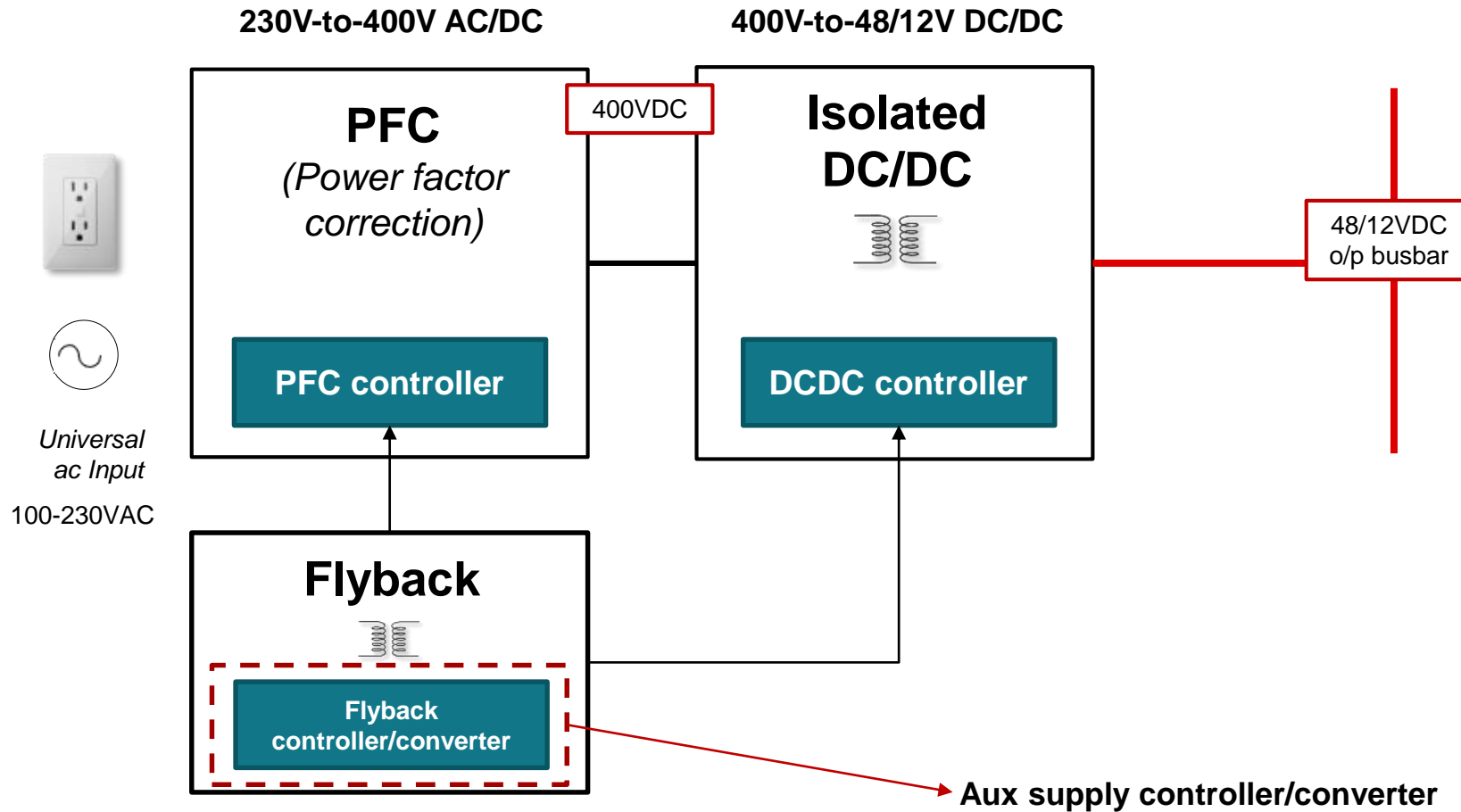
Flexible digital power controller → easy wide EE & economies of scale

Advanced housekeeping functions

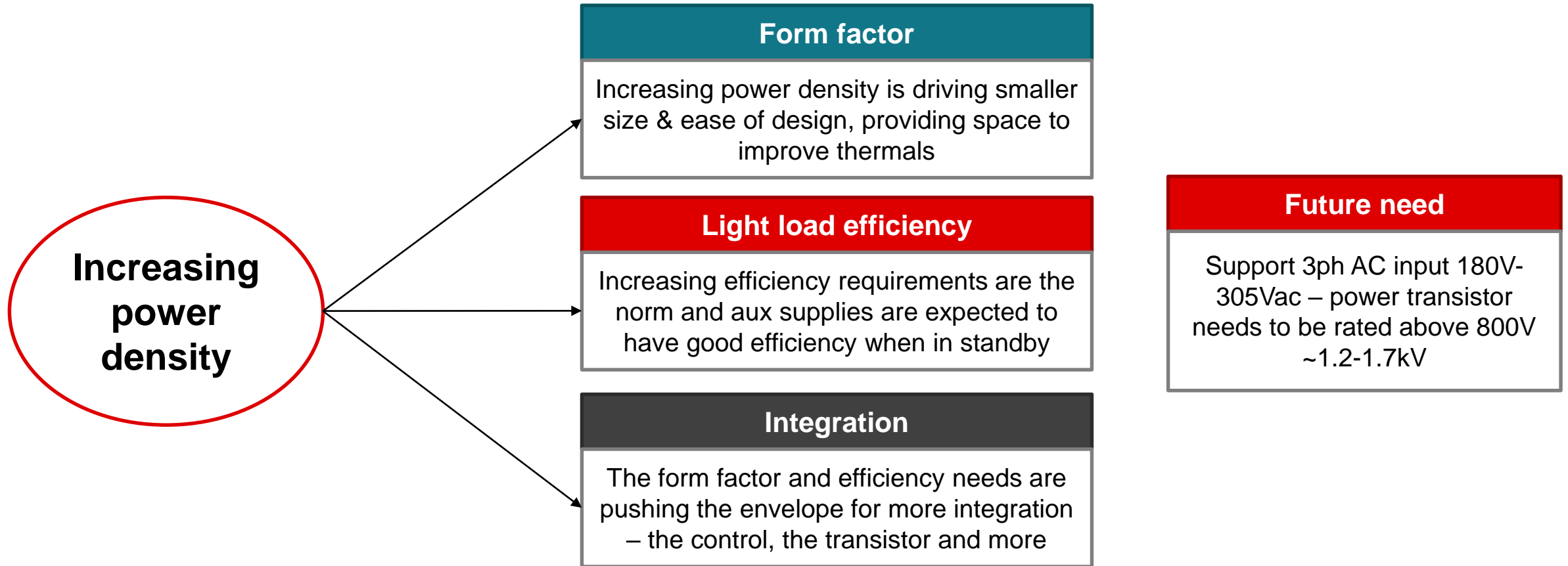


GP-ADC + Arm-MCU + Comms. → superior system integration

Typical server power supply control uses individual controllers at each stage

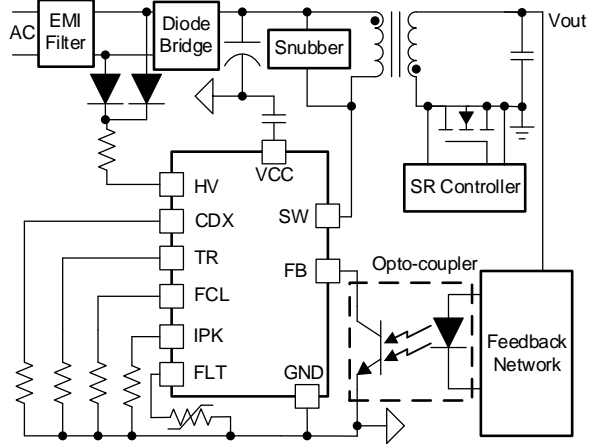


Key aux supply concerns in server power

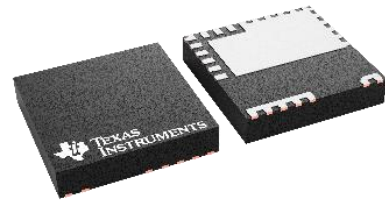


UCG28826 | TI's first GaN integrated flyback

UCG28826: Industry's first self-biasing flyback converter



- ▶ **Integrated 650-V GaN** with built-in current sense
- ▶ **Enables lowest system cost** with cutting-edge feature integration
- ▶ **Improved efficiency, EMI, and design flexibility**



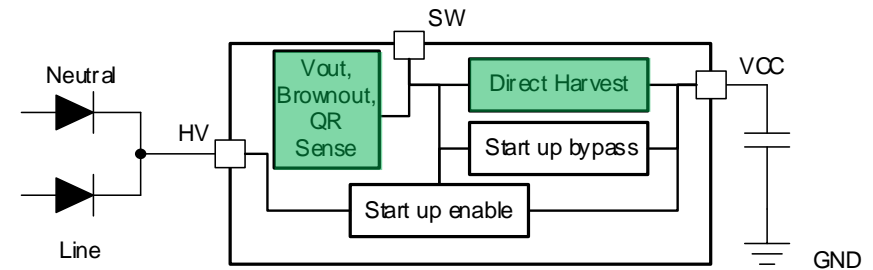
Industry-leading features for flyback converters

- ▶ Self-bias and sensing for **auxless converter design**
- ▶ Dynamic CCM/QR/DCM control law for **optimized variable-load efficiency**
- ▶ Switching slew rate control for **EMI mitigation**
- ▶ **Comprehensive protections** including OTP, OVP, OCP, OPP, Brownout, etc.
- ▶ **Leading design flexibility** including frequency clamping, fault response, etc.

Innovative self-bias & auxless-sensing scheme

Completely eliminate auxiliary winding and VCC pre-regulator

- ▶ Naturally harvest bias energy from power stage
- ▶ Direct switch-node sensing



- ✓ Higher integration
- ✓ Higher efficiency
- ✓ Smaller size
- ✓ Reduced cost
- ✓ Simplified design



UCG28826EVM-093: 65-W integrated GaN flyback converter

Available NOW

Key specifications

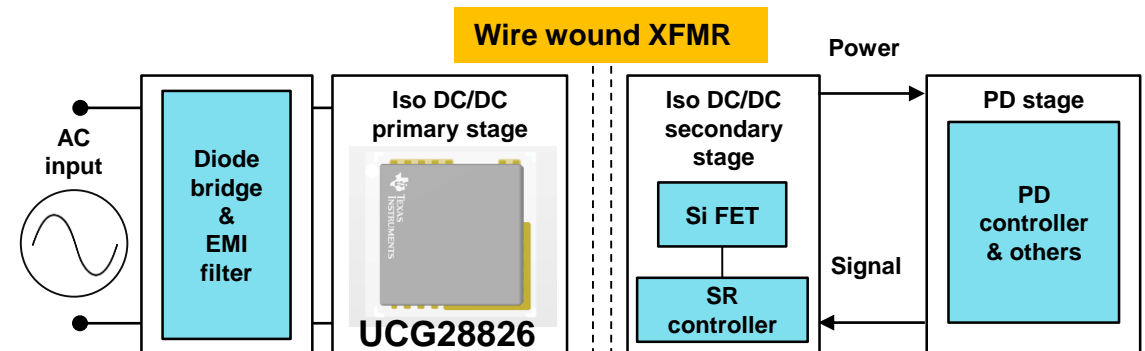
- Input voltage: 90 to 264VAC
- Max output power: 65W
- Output voltage range: 5-20Vdc
- PD output: 5V/3A, 9V/3A, 15V/3A, 20V/3.25A
- EMC compliance CISPR32B / EN55032B
- Average efficiency and standby power to meet DoE level VI and CoC Tier 2 limits
- Peak efficiency > **94%**
- Power density: **2.84W/cm³** without case
- Profile: **Cubicle**
- Form factor w/o case: **3.93cm x 3.45cm x 1.7cm = 23cm³**
- Form factor w/case: **4.33cm x 3.95cm x 2.1cm = 36cm³**

Applications

- High density PSU
- Cell phone chargers
- Notebook adapters

Benefits

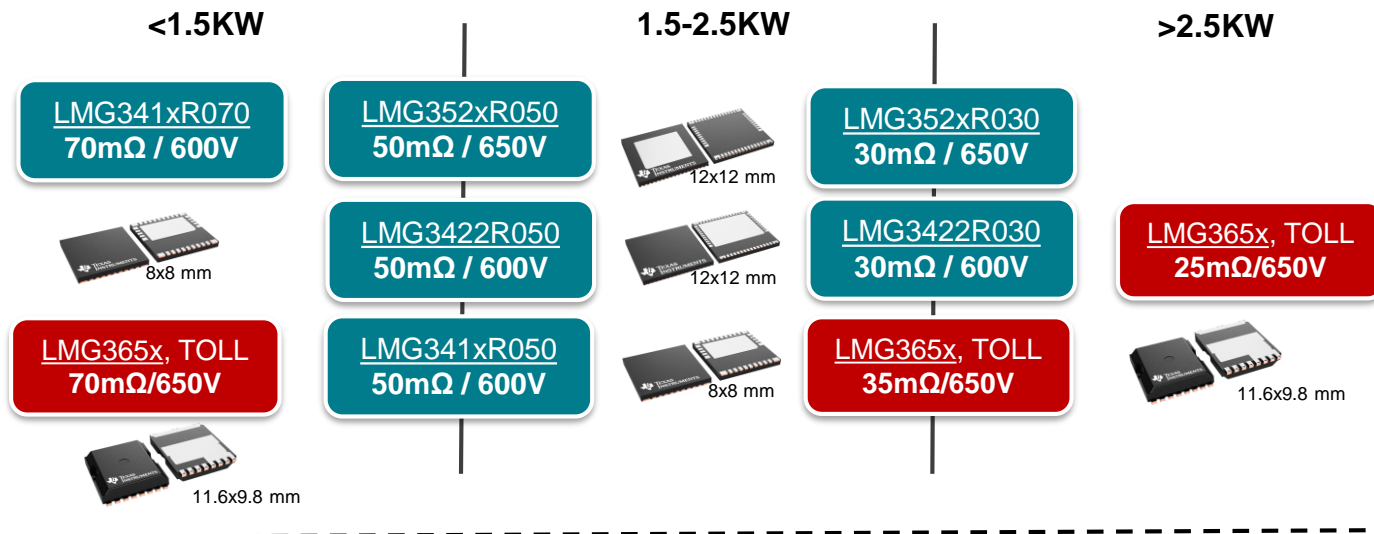
- Auxless design enables lower component count, higher density
- Supports USB-PD charging protocol
- Quasi-resonant operation with adjustable valley switching function to maximize efficiency at any line and load condition
- SSR topology implementation with an opto-coupler for accurate step voltage control



PFC/ISO device selection guide

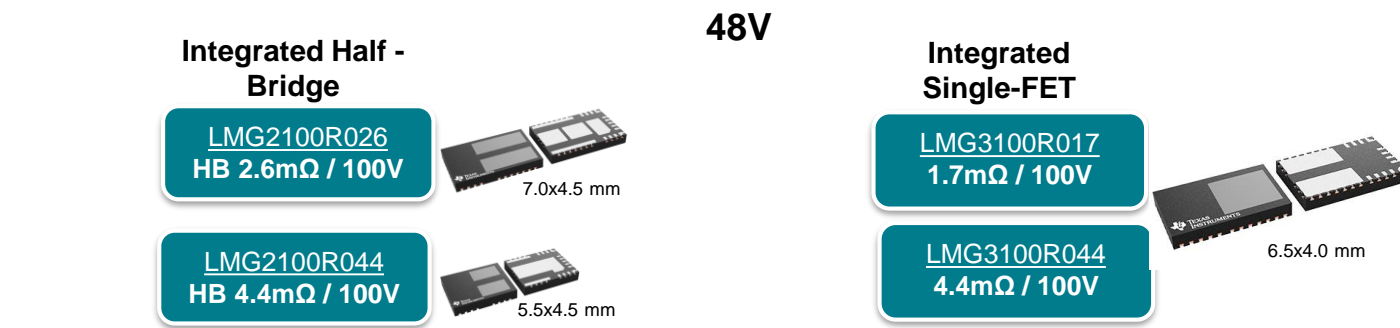
High Voltage Device Portfolio

PFC/ISO primary device selection



Medium Voltage Device Portfolio

ISO secondary device selection



Production

Samples

Controller selection

Main power stage

UCD3138A (40/64/80p)
 3HS loops, 8 DPWMs, 450ns latency, ARM7TDMI, 31.25MHz, upto 128k dual bank flash, 2k D-flash, 8k RAM, upto 43 GPIOs, 15 ADCs

TMS320F28003x
 32bit DSP core @ 120MHz
 384KB (192KW) of flash (ECC-protected)
 69KB (34.5KW) of RAM (ECC-protected)
 16 ePWM channels w/ 8 channels having high-res capability (150-ps resolution)

Aux supply

UCG28826x
 65W (45/120W), SSR, HVSU, GaN-integrated

UCC28742
 SSR, high eff., 1% o/p regulation

UCC28740
 SSR, CVCC, HVSU, 100kHz max.

UCC28730
 PSR, CVCC, wake up monitor

All samples and associated reference designs / EVMs available on ti.com; click on a device name to be redirected.



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